

## Control Devices: MMN 7000 Series (Continued)

## Electrical Characteristics

## High Power Switching &amp; Attenuation

$V_{br}^1$ MIN (V)	$C_{j-10} V^2$ MAX (pF)	$T_f^3$ TYP ( $\mu$ S)	$R_s^5@$ 1 mA MAX (Ohms)	$R_s^5@$ 10 mA MAX (Ohms)	$R_s^5@$ 100 mA MAX (Ohms)	$\theta_{jc}$ MAX $^{\circ}$ C/W	Part Number
250	.08	1.0	20	8	1.5	20	MMN7061
250	.2	1.0	8	3.5	1.0	15	MMN7063
500	.1	1.5	15	5	1.2	15	MMN7066
500	.3	2.0	8	3.5	0.8	10	MMN7068

## Notes:

1. Reverse Breakdown Voltage measured at 10 $\mu$ A.
2. Junction Capacitance measured at -10 volts at 1 MHz.
3. Minority Carrier lifetime measured with IF = 10 mA, IR = 6mA.
4. RF Switching speed measured from 90% to 10% and 10% to 90% transmission. Drive output = +20 mA and -4 volts, 200 mA spike with a rise time of 2 nS.
5. Series Resistance is measured at 1 GHz using transmission loss techniques.

## Maximum Ratings

Operating Temperature	-55 $^{\circ}$ C to 150 $^{\circ}$ C
Storage Temperature	-65 $^{\circ}$ C to 200 $^{\circ}$ C
Reverse Breakdown Voltage ( $V_{br}$ )	from 25 volts to 500 volts at 10 $\mu$ A
Junction Capacitance ( $C_{j-10}$ )	from .07 to .5 pF at 10 volts
Switching Speed ( $T_f$ )	from 1 nS to 25 nS
Lifetime (TI)	from 10 nS to 2.0 $\mu$ S TYP
Chip Thickness	.004" - .007" thick